

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

SHANMUGASUNDRAM et al.

Serial No. 09/943,383

Filed: August 31, 2001

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Group Art Unit: 2823

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Examiner: William D. Coleman

For: IN SITU SENSOR BASED CONTROL OF SEMICONDUCTOR PROCESSING
PROCEDURE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right

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Serial No. 09/943,383

to present to the Office the relevant facts and law regarding the appropriate status of such document.

Please charge the fee of \$180.00 under 37 CFR 1.17(p) to Deposit Account No. 08-0219. The Commissioner is authorized to charge any deficiency in any fees pursuant to 37 CFR § 1.17 associated with this communication and to credit any excess payment to Deposit Account No. 08-0219.

Respectfully submitted,

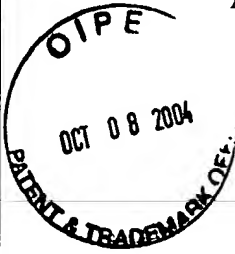
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<p style="text-align: center;">INFORMATION DISCLOSURE CITATION IN AN APPLICATION</p> <p style="text-align: center;">(PTO-1449)</p> 		ATTY. DOCKET NO. 005920 USA/ PMG/PCTRL	SERIAL NO. 09/943,383
		APPLICANT SHANMUGASUNDRAM et al.	
		FILING DATE August 31, 2001	GROUP 2823
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
	IslamRaja, M. M., C. Chang, J. P. McVittie, M. A. Cappelli, and K. C. Saraswat. May/June 1993. "Two Precursor Model for Low-Pressure Chemical Vapor Deposition of Silicon Dioxide from Tetraethylorthosilicate." <i>J. Vac. Sci. Technol. B</i> , Vol. 11, No. 3, pp. 720-726.		
	Kim, Eui Jung and William N. Gill. July 1994. "Analytical Model for Chemical Vapor Deposition of SiO ₂ Films Using Tetraethoxysilane and Ozone" (Abstract). <i>Journal of Crystal Growth</i> , Vol. 140, Issues 3-4, pp. 315-326.		
	Guo, R.S., A. Chen, C.L. Tseng, I.K. Fong, A. Yang, C.L. Lee, C.H. Wu, S. Lin, S.J. Huang, Y.C. Lee, S.G. Chang, and M.Y. Lee. June 16-17, 1998. "A Real-Time Equipment Monitoring and Fault Detection System." <i>Semiconductor Manufacturing Technology Workshop</i> , pp. 111-121.		
	Lantz, Mikkel. 1999. "Equipment and APC Integration at AMD with Workstream." <i>IEEE</i> , pp. 325-327.		
	July 15, 2004. Office Action for U.S. Serial No. 10/172,977, filed June 18, 2002.		
	August 2, 2004. Office Action for U.S. Serial No. 10/174,377, filed June 18, 2002.		
	August 9, 2004. Written Opinion for PCT Serial No. PCT/US02/19063.		
	August 18, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US02/19116.		
	August 24, 2004. Office Action for U.S. Serial No. 10/135,405, filed May 1, 2002.		
	August 25, 2004. Office Action for U.S. Serial No. 09/998,384, filed November 30, 2001.		
	September 9, 2004. Written Opinion for PCT Serial No. PCT/US02/21942.		
	September 16, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US02/24859.		
EXAMINER		DATE CONSIDERED	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.